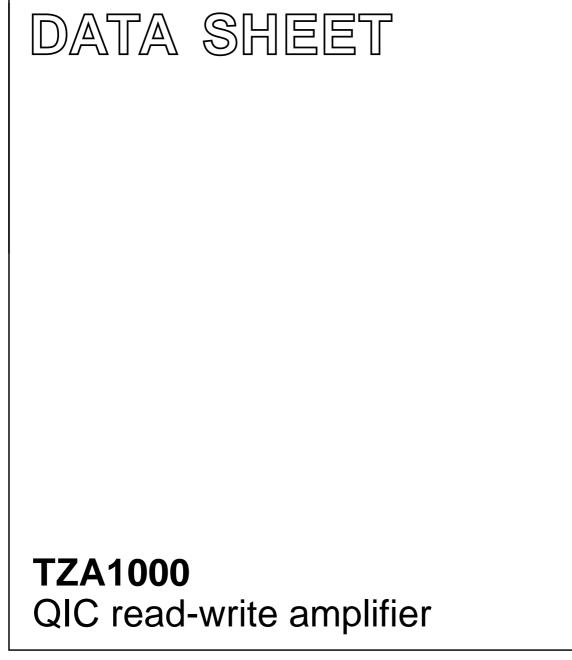
# INTEGRATED CIRCUITS



Preliminary specification Supersedes data of 1998 Mar 11 File under Integrated Circuits, IC01 1998 Mar 17



HILIP

# TZA1000

#### FEATURES

- 3-wire serial interface for programming
- On-chip Digital-to-Analog Converters (DAC) for:
  - MR (Magneto Resistive) sense bias current
  - MR DC bias current
  - Write current
- Low noise differential input stage: typically 0.65 nV/ $\sqrt{Hz}$  (Z<sub>i</sub> = 0  $\Omega$ )
- Magnetic feedback circuit to handle large output signals
- MR DC bias current circuit
- Very fast write current rise and fall times with near rail-to-rail voltage swing
- Maximum write current of 100 mA: ready for high coercivity tape
- Low noise read amplifier for reading track height servo signals with the write coil
- Very few external components required
- On board registers for easy format or bit rate selection
- Fast read-after-write recovery time
- Test circuit for yoke-type heads
- Switchable differentiator for yoke-type heads, with programmable cut-off frequencies
- Anti-aliasing low-pass filter, with programmable cut-off frequencies
- AGC (Automatic Gain Control) options: internally (digitally) controlled, externally controlled or fixed gain
- Hold input for fast AGC freeze

- Input for fast reader/writer (track height servo) signal selection
- Power fail detection on both 5 and 12 V lines (status can be read from the read register)
- Write unsafe detection
- Provides an accurate reference voltage (for AD conversion)
- Very simple interconnection with the SZA1000 QIC digital equalizer
- +5 V  $\pm 10\%$  and +12 V  $\pm 10\%$  supply voltages
- Low power standby, active and test modes.

#### **RELATED DOCUMENTS**

- SZA1000 QIC digital equalizer data sheet
- Application notes for TZA1000 and SZA1000.

Both are available from Philips Semiconductors.

#### **GENERAL DESCRIPTION**

The TZA1000 is a single-chip read-write amplifier for single-channel QIC (Quarter Inch Cartridge) systems with MR heads. It can be used with both SIG (Sensor in Gap)and yoke-type MR heads and is designed to be used in conjunction with the Philips SZA1000 digital equalizer IC (although it can also function as a stand alone unit). This combination is flexible enough to be used with all popular tape backup formats including QIC 80, QIC 3010, QIC 3020, QIC 3080, QIC 5010, Travan 1, Travan 2, Travan 3 and Travan 4 and to be forward compatible with their single channel successors.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DD1</sub>	read circuit supply voltage		4.5	5	5.5	V
V <sub>DD2</sub>	FB and write circuit supply voltage		4.5	5	5.5	V
V <sub>DD3</sub>	sense current circuit supply voltage		10.8	12	13.2	V
I <sub>DD1</sub> ; I <sub>DD2</sub>	read/FB and write circuit supply current					
	Read mode		-	69	-	mA
	Write mode	I <sub>write</sub> = 30 mA	-	105	_	mA
I <sub>DD3</sub>	sense current circuit supply current	I <sub>sense</sub> = 16 mA	15.0	16.2	19.0	mA
V <sub>n(i)(eq)</sub>	equivalent input noise voltage	$Z_{source} = 0 \Omega$	-	0.65	0.8	nV/√Hz
f <sub>clk</sub>	clock frequency		-	-	24	MHz
T <sub>amb</sub>	recommended operating temperature		0	-	70	°C
Tj	recommended junction temperature		0	-	125	°C
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	66	_	K/W

#### QUICK REFERENCE DATA

# TZA1000

#### ORDERING INFORMATION

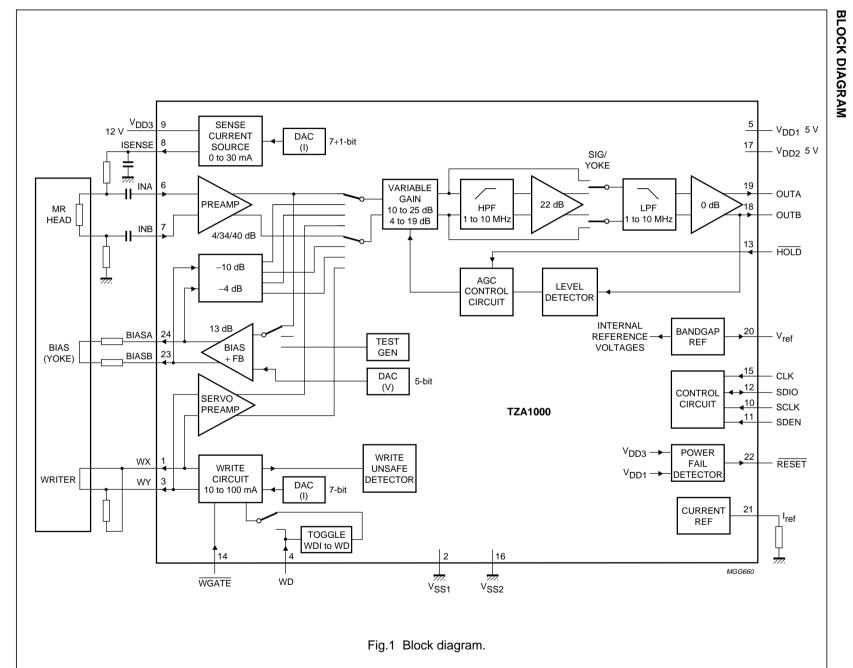
TYPE		PACKAGE	VERSION	
NUMBER	NAME	DESCRIPTION	VERSION	
TZA1000	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1	



# Preliminary specification

# QIC read-write amplifier

# TZA1000



1998 Mar 17

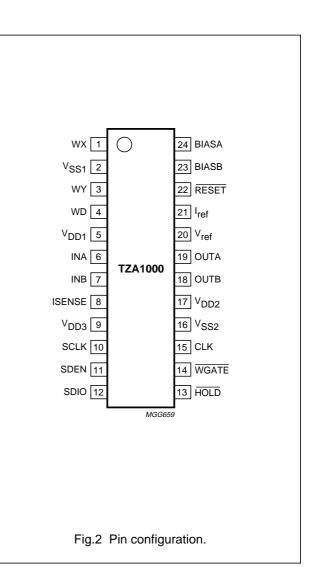
\_

4

# TZA1000

#### PINNING

SYMBOL	PIN	DESCRIPTION	TYPE <sup>(1)</sup>
WX	1	write current to head	0
V <sub>SS1</sub>	2	large signal ground	Р
WY	3	write current to head	0
WD	4	write data	<b> </b> (2)
V <sub>DD1</sub>	5	large signal +5 V	Р
INA	6	read signal from MR	1
INB	7	read signal from MR	1
ISENSE	8	sense current for MR	0
V <sub>DD3</sub>	9	+12 V for sense current supply	Ρ
SCLK	10	serial interface clock	<b> </b> (2)
SDEN	11	serial interface enable	<b> </b> (2)
SDIO	12	serial interface data I/O	I/O
HOLD	13	hold AGC; active LOW	<b> </b> (2)
WGATE	14	write gate; active LOW	<b> </b> (2)
CLK	15	clock input	<b> </b> (2)
V <sub>SS2</sub>	16	small signal ground	Р
V <sub>DD2</sub>	17	small signal +5 V	Р
OUTB	18	output to equalizer	0
OUTA	19	output to equalizer	0
V <sub>ref</sub>	20	2 V reference output	0
I <sub>ref</sub>	21	current reference resistor	note 3
RESET	22	reset for microcontroller; active LOW	0
BIASB	23	bias current for yoke heads	0
BIASA	24	bias current for yoke heads	0



#### Notes

- Pin type abbreviations: O = output, I = input, P = power supply.
- 2. Digital inputs: LOW:  $<0.3V_{DD}$ ; HIGH:  $>0.7V_{DD}$ .
- 3. Use only for connecting current reference resistor.

See Chapter "Equivalent pin circuits" for the I/O configuration of the analog pins.

# TZA1000

#### FUNCTIONAL DESCRIPTION

#### The preamplifier

The gain and dynamic range of the symmetrical low noise preamplifier can be varied to accommodate a wide variation in input signal amplitude (see Table 11). The 40 dB and 34 dB gain settings are provided for normal use. The 40 dB setting offers the lowest noise figure. The 4 dB gain setting is intended for IC testing only.

#### The servo preamplifier

This low noise preamplifier can be used for reading signals, such as QIC 3095 (Travan 4) servo signals, via the recording head write coil. Servo mode is selected either by resetting bits AI0 and AI1 in the control register (see Table 9) or by means of the HOLD pin (the HSM control bit must be set when HOLD goes LOW; see Table 7). When servo mode is selected, the maximum total gain is set automatically regardless of, and without overwriting, gain settings. Fast switch-over from read mode to servo mode can thus be achieved without having to alter register values.

#### Variable gain stage and AGC

The input to the variable gain stage can be switched to the preamplifier output, to the output of the bias/FB (Feed Back) circuit, or to the servo preamplifier output. When using magnetic feedback, the bias/FB circuit output should be selected (see Table 9).

The AGC range is 15 dB. The gain is programmable in 1 dB steps (see Table 12). If the output signal is too small, a digital control circuit will increase the gain from minimum to maximum in approximately 10 ms. If the output signal is too large, the gain will be reduced from maximum to minimum in approximately 0.2 ms. These values assume a 24 MHz clock frequency. The upper limit of the gain control range can be extended by 6 dB by setting the G6DB bit in the control register via the serial interface (see Table 13).

The AGC is frozen while the HOLD input is LOW, the TZA1000 is writing, or the IC is in servo mode.

The AGC can be operated internally, running on the CLK clock signal on pin 15 (HOLD HIGH and GFXD LOW; see Table 12), or externally by means of a software algorithm (GFXD HIGH). When operated externally, either the DN bit in the status read register (see Table 17) or the level measurement in the digital equalizer IC (SZA1000) can be used as input to the algorithm.

The AGC will maintain outputs OUTA and OUTB at 1.1 V (p-p). Additional level adjustment points are provided by the 34 or 40 dB preamplifier gain switch (see Table 11) and the -10 or -4 dB bias output attenuation switch (see Table 9).

#### High-pass filter

The HPF (High-Pass Filter) is used to differentiate yoke-type head signals. It is followed by an additional gain stage (21 dB). The HPF cut-off frequency is coupled to the cut-off frequency of the LPF (Low-Pass Filter), and is selectable in 4 steps: 1, 2, 4 and 10 MHz (see Table 2). The HPF can be bypassed for SIG heads (see Table 8).

#### Low-pass filter

The second order low-pass filter is used to attenuate high frequency noise above the signal bandwidth, mainly to provide anti-aliasing filtering for the A/D converter in the digital equalizer. The cut-off frequency of the LPF is selectable in 4 steps: 1, 2, 4 and 10 MHz (see Table 2).

#### Sense current circuit

The sense current circuit is a programmable current source, operating from the 12 V supply ( $V_{DD3}$ ). It can be programmed to supply a current between 0 and 15 mA, with 7-bit resolution. The current range can be doubled, then ranging from 0 to 30 mA, by setting the SDB bit in the control register (see Table 15). The sense current circuit can be disabled by resetting the ENS bit (see Table 4).

This is the only circuit on the IC that uses the 12 V supply. The output must be decoupled with a low impedance capacitor (10  $\mu F$  recommended) to reduce noise coupling into the head.

For the current source circuit to operate correctly, the voltage difference between  $V_{DD3}$  (pin 9) and ISENSE (pin 8) must be at least 1.6 V.

#### Bias and magnetic feedback circuit

This circuit can be used to generate AC and DC bias currents (for a yoke-type MR head, for instance). The DC bias output voltage is programmable between 0 and 1.4 V, with 5-bit resolution (see Table 3). The DC current generated is this voltage divided by the total bias resistance (head coil + total series resistance).

The AC signal input to the circuit can be switched to the preamplifier output (see Table 10). In this way, magnetic feedback inside the head can be achieved. This limits head distortion, and prevents head saturation from large tape signals, like QIC 80 recordings.

The open loop gain of the feedback loop depends on head sensitivity, the selected sense current (see Table 15), and the selected preamplifier gain (see Table 11). The values of the external resistors connected in series with the bias conductor can be used to set the gain. For loop stability at high frequencies, the bandwidth of the magnetic feedback amplifier is limited to 5 MHz.

In closed loop mode, the effective cut-off frequency for the playback signals will increase with the feedback factor. For this reason the read signal can be taken from the output of the bias circuit.

To prevent loop instability at low frequencies, the preamplifier input capacitors should be chosen such that the cut-off frequency at that point is well above, or well below, the internal cut-off frequency of the AC coupling between the preamplifier and the bias circuit (input impedance of the preamplifier is typically  $2 \text{ k}\Omega$ ).

The maximum (peak AC) current that the bias circuit can deliver can be adjusted to achieve an optimum balance between required current range and power consumption (see Table 3). The AC circuit is switched off when the TZA1000 is writing, and the maximum current is switched to 10 mA. This limits power dissipation during writing.

#### **Test generator**

This circuit generates a test signal with a frequency  $\frac{1}{16}$  that of the signal at the CLK input (pin 15). By switching the AC input of the bias circuit to the internal test generator (see Table 10), the read channel can be tested. The differential output value is typically 100 mV (p-p).

This facility can also be used to adjust the DC bias voltage while monitoring the signal at the read element in the head. The optimum DC bias level setting is just before the output from the read head reaches its peak.

#### Write circuit

The write circuit is a differential current source that can generate a near rail-to-rail output voltage to get the shortest current transition time. Writing is enabled when WGATE is LOW. The polarity of the current depends on the WD input pin. The WDM bit in the control register determines the write signal mode: WD (Non-Return to Zero) or WDI (Return to Zero; see Table 14). When WDI mode is selected, the polarity of the write current is reversed at every falling edge of the WD input. When WD mode is selected, the polarity of the write current is reversed when the polarity of WD changes. The write current is programmable between 0 and 125 mA, with 7-bit resolution (see Table 14).

The IC is specified for a write current of up to 100 mA. Overshoot caused by an inductive load can be minimized by means of a single external resister local to the IC.

#### Write unsafe detector

The write unsafe detector will detect an open write coil, or one shorted to ground. The circuit is enabled only while the TZA1000 is writing. A resistance to GND or V<sub>DD</sub> of less than 10  $\Omega$ , or a series resistance greater that about 300  $\Omega$ , will be detected (these values are write-current dependant). If an error occurs, the WUS status bit is set. This bit can be read via the serial interface. The WUS bit will remain set until the status byte is read.

#### Power fail detector

The power fail detector will detect a low voltage on the 5 V  $(V_{DD1})$  or 12 V  $(V_{DD3})$  supply lines. The thresholds are 3.75 V for  $V_{DD1}$  and 9 V for  $V_{DD3}$ . A power failure is detected if the voltage is below the threshold for 1  $\mu$ s or longer. If a 5 V power failure occurs, the status bit PF5 is set. If a 12 V power failure occurs, the status bit PF12 is set. These bits can be read via the serial interface, and will remain HIGH until the status byte is read.

When a 5 V power failure occurs, the RESET output goes LOW and the write circuit is disabled (in addition to PF5 being set). The RESET output has an internal 18 k $\Omega$  pull down resistor to guarantee a LOW level at the output even when a power failure occurs. During normal operation, the RESET pin should not be held LOW by an external circuit, since this will switch the IC into test mode.

### TZA1000

# TZA1000

#### DACs

There are 3 internal DACs:

- 1. The Sense DAC: current DAC; 7-bit resolution
- 2. The Write DAC: current DAC; 7-bit resolution
- 3. The Bias DAC: voltage DAC; 5-bit resolution.

The Sense and Write DAC current settings are a function of the reference current  $I_{ref}$  (at the  $I_{ref}$  pin).  $I_{ref}$  is multiplied by a 7-bit factor: S0 to S6 for the sense DAC, W0 to W6 for the write DAC (see Tables 14 and 15). If the resistance between  $I_{ref}$  and GND is increased (or decreased), the DAC output currents will be decreased (or increased) by the same factor. In this way, the DAC output current ranges can be adjusted.

The current values specified, and the equations used to calculate Sense and Write currents (see Tables 14 and 15), are for a 430  $\Omega$  resistance between  $I_{ref}$  and GND. This resistance can be varied between 250  $\Omega$  and 1 k $\Omega$ , giving a  $\pm 2 \times$  DAC modification range. For reasons of noise and stability, the voltage at the  $I_{ref}$  pin should not be used in any other part of the circuit.

#### **Clock handling**

The TZA1000 has 2 clock inputs:

CLK: the general clock input, pin 15

SCLK: the serial interface clock input, pin 10.

CLK is used for status register read and write cycle timing and for operating the internal AGC. When the AGC is not being used and serial communications are not active, CLK may be switched off. This can help reduce crosstalk on the printed circuit board.

When accessing the status register, the CLK frequency must be at least  $16 \times$  SCLK frequency. It is recommended that the 24 MHz clock supplied by the SZA1000 be used directly.

#### Serial interface

The 3 wire serial interface recognizes 8-bit addresses and 8-bit data. To read data from the status register, hex address FF must be transmitted. The IC will then respond with the contents of the 8-bit status register.

QIC read-write amplifier WRITE SETTINGS SDEN 3-STATE  $- \left( A7 \right) \left( A6 \right) \left( A5 \right) \left( A4 \right) \left( A3 \right) \left( A2 \right) \left( A1 \right) \left( A0 \right) \left( D7 \right) \left( D6 \right) \left( D5 \right) \left( D4 \right) \left( D3 \right) \left( D2 \right) \left( D1 \right) \left( D0 \right) \left( D5 \right) \left( D4 \right) \left( D3 \right) \left( D2 \right) \left( D1 \right)$ SDIO READ STATUS SDEN 3-STATE - (A7 ) A6 ) A5 ) A4 ) A3 ) A2 ) A1 ) A0 ) D7 ) D6 ) D5 ) D4 ) D3 ) D2 ) D1 ) D0 - (D7 ) D6 ) D5 ) D4 ) D3 ) D2 ) D1 ) D0 SDIO ADDRESS AND DATA FROM MICROCONTROLLER DATA FROM IC MGG661 TZA1000 Fig.3 Timing diagrams.

Philips Semiconductors

9

1998 Mar 17

Preliminary specification

TZA1000

#### **CONTROL REGISTER**

The control register contains six 8-bit entries configured as shown in Table 1.

ADDRESS	D7	D6	D5	D4	D3	D2	D1	D0
0	_	FC1	FC0	ENFB1	ENFB0	ENS	ENRD	ENREF
1	HSM	DIFF	Al1	AI0	FBI1	FBI0	PG1	PG0
2	_	-	G6DB	GFXD	G3	G2	G1	G0
3	-	-	-	B4	B3	B2	B1	B0
4	WDM	W6	W5	W4	W3	W2	W1	W0
5	SDB	S6	S5	S4	S3	S2	S1	S0

#### Table 1 Control register settings

#### **Control bits**

Control bit functions are detailed in Tables 2 to 17.

#### Table 2 HPF and LPF cut-off frequency

FC1	FC0	FREQUENCY
0	0	1 MHz
0	1	2 MHz
1	0	4 MHz
1	1	10 MHz

#### Table 3 Bias current settings; note 1

ENFB1	ENFB0	BIAS CIRCUIT	I <sub>bias(min)</sub>	I <sub>bias(max)</sub>
0	0	off	0	0
0	1	on	–10 mA	+10 mA
1	0	on	0	+10 mA
1	1	on	–10 mA	+20 mA

#### Note

1. Control bits B0 to B4 make up a 5-bit number between 0 and 31. The DC bias voltage between BIASA and BIASB (pins 23 and 24) is B × 45 mV. BIASA is positive with respect to BIASB.

#### Table 4Sense current circuit

ENS	SENSE CURRENT CIRCUIT
0	disabled
1	enabled

Table 5	Read circuits	(excluding	preamplifiers)
---------	---------------	------------	----------------

ENRD	READ CIRCUITS
0	disabled
1	enabled

#### Table 6 Internal reference voltages

ENREF	INTERNAL REF. VOLTAGES
0	disabled
1	enabled

#### Table 7 HOLD pin function

HSM FUNCTION	
0	AGC hold on or off
1	select servo or data preamplifier

# TZA1000

Table 8 HPF circuit

DIFF	HPF CIRCUIT
0	bypassed
1	on

#### Table 9 Variable gain circuit input select

HSM	HOLD	Al1	AI0	INPUT		
0	Х	0	0	servo preamplifier		
0	Х	0	1	preamplifier		
0	Х	1	0	bias output –10 dB		
0	Х	1	1	bias output –4 dB		
1	1	0	0	servo preamplifier		
1	1	0	1	preamplifier		
1	1	1	0	bias output –10 dB		
1	1	1	1	bias output –4 dB		
1	0	Х	Х	servo preamplifier		

#### Table 10 Bias circuit input

# FBI1FBI0INPUT00no signal01preamplifier10test generator11preamplifier

#### Table 11 Preamplifier gain

PG1	PG0	GAIN
0	0	0
0	1	34 dB
1	0	4 dB
1	1	40 dB

#### Table 12 AGC setting

HSM	HOLD	GFXD	AGC
0	1	0	on
0	0	0	frozen at last value
1	1	0	on
1	0	0	no AGC at servo mode: maximum gain
Х	Х	1	off, gain set by G0 to G3; note 1

#### Note

1. Control bits G0 to G3 make up a 4-bit number used to program the gain in 1 dB steps (from 4 to 19 dB if G6DB is 0, from 10 to 25 dB if G6DB is 1; see Table 13).

Table 13	Variable	gain	circuit	range	select
----------	----------	------	---------	-------	--------

G6DB	RANGE
0	4 to 19 dB
1	10 to 25 dB

# TZA1000

Table 14 Write mode select; note 1

WDM	EXPECTED INPUT SIGNAL	FUNCTION
0	WDI	on
1	WD	bypassed

#### Note

1. Control bits W0 to W6 make up a 7-bit number between 0 and 127. Write current is

 $\frac{125 \times (W+1)}{128} \text{ mA } (R_{ref} = 430 \ \Omega).$ 

#### Table 15 Sense current range select; note 1

SDB	CURRENT
0	0 to 15 mA
1	0 to 30 mA

#### Note

1. Control bits S0 to S6 make up a 7-bit number between 0 and 127. Sense current is  $\frac{15 \times (S+1)}{128}$  mA when SDB = 0

and 
$$\frac{30 \times (S+1)}{128}$$
 mA when SDB = 1 (R<sub>ref</sub> = 430  $\Omega$ ).

#### Status

A status byte, located at address FF, contains the following status bits:

#### Table 16 Status byte settings

ADDRESS	D7	D6	D5	D4	D3	D2	D1	D0
FF	AG3 <sup>(1)</sup>	AG2 <sup>(1)</sup>	AG1 <sup>(1)</sup>	AG0 <sup>(1)</sup>	DN <sup>(2)</sup>	PF5 <sup>(3)</sup>	WUS <sup>(4)</sup>	PF12 <sup>(5)</sup>

#### Notes

- 1. Actual gain. Allows the gain to be determined while the AGC is on.
- 2. This bit can be used for microcontroller gain control, with the AGC off (see Table 17).
- 3. Power failure detected on the +5 V supply ( $V_{DD1}$ ).
- 4. Write unsafe detected: head open or short circuited.
- 5. Power failure detected on the +12 V supply ( $V_{DD3}$ ).

#### Table 17 Sense current range select.

DN	GAIN
0	can be increased
1	can be decreased

TZA1000

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>DD1</sub>	read circuit supply voltage		-0.3	+5.5	V
V <sub>DD2</sub>	FB and write circuit supply voltage		-0.3	+5.5	V
V <sub>DD3</sub>	sense current circuit supply voltage		-0.3	+13.2	V
I <sub>DD1</sub>	read circuit supply current		-	150	mA
I <sub>DD2</sub>	FB and write circuit supply current		-	35	mA
I <sub>DD3</sub>	sense current circuit supply current		-	35	mA
I <sub>I(n)</sub>	input current on remaining pins		-10	+10	mA
P <sub>tot</sub>	maximum total power dissipation		-	1000	mW
T <sub>amb</sub>	ambient temperature		0	+70	°C
Tj	junction temperature	note 1	0	+135	°C
T <sub>stg</sub>	storage temperature		-50	+150	°C
V <sub>ES(HB)</sub>	electrostatic handling: human body model	note 2	-1000	+1000	V
V <sub>ES(MM)</sub>	electrostatic handling: machine model	note 3	-200	+200	V

#### Notes

- 1. Maximum permissible ambient temperature is dependent on internal dissipation. T<sub>j</sub> is the discriminating factor.
- $T_j = (R_{th(j-a)} \times P_{tot}) + T_{amb}$ , where  $P_{tot}$  is the total dissipation in the package.
- 2. Equivalent to discharging a 100 pF capacitor through a 1.5 k $\Omega$  series resistor.
- 3. Equivalent to discharging a 200 pF capacitor through a 25  $\Omega$  series resistor and a 2.5  $\mu$ H series inductance.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient in free air	66	K/W

#### **QUALITY SPECIFICATION**

In accordance with "SNW-FQ-611E".

# TZA1000

#### CHARACTERISTICS

 $V_{DD1}$  =  $V_{DD2}$  = 5 V ±5%;  $V_{DD3}$  = 12 V ±5%;  $T_{amb}$  = 25 °C ±5%; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DD1</sub>	read circuit supply voltage		4.5	5.0	5.5	V
V <sub>DD2</sub>	FB and write circuit supply voltage		4.5	5.0	5.5	V
V <sub>DD3</sub>	sense current circuit supply voltage		10.8	12.0	13.2	V
I <sub>DD1</sub>	read circuit supply current					
	Rd	$I_{bias} = -10$ to +10 mA	-	31	-	mA
	Wr	I <sub>write</sub> = 30 mA	_	70	-	mA
I <sub>DD2</sub>	FB and write circuit supply current					
	Rd	max gain	_	38	-	mA
	Wr		-	36	-	mA
I <sub>DD3</sub>	sense current circuit supply current	I <sub>sense</sub> = 16 mA	15.0	16.2	19.0	mA
V <sub>ref</sub>	reference voltage	pin 20; I <sub>O</sub> = 0 to 3 mA	1.9	2.0	2.1	V
I <sub>20</sub>	current on pin 20 (V <sub>ref</sub> )					
	source		_	_	3.0	mA
	sink		-	-	50	μA
V <sub>21</sub>	voltage at pin 21 (I <sub>ref</sub> )		1.2	1.3	1.4	V
I <sub>ref</sub>	reference current (pin 21)		1	3	5	mA
Read section					•	•
G <sub>v(pa)</sub>	preamplifier voltage gain	PG1 = 1; PG0 = 1	37	38.6	41	dB
. , , , , , , , , , , , , , , , , , , ,		PG1 = 0; PG0 = 1	32	32.7	34	dB
		PG1 = 1; PG0 = 0	3	4.1	6	dB
G <sub>v(agc)</sub>	AGC amplifier voltage gain	G6DB = 1; G = 15; note 1	23	24.4	26	dB
$\Delta G_{v(agc)}$	AGC voltage gain control range	note 2	-	22	-	dB
G <sub>v(yoke)</sub>	yoke amplifier voltage gain		19	21	23	dB
f <sub>coupling</sub>	-3 dB AC coupling frequency	input to output	2	5	10	kHz
f_3dB(cutoff)(HPF)	HPF –3 dB cut-off frequency	FC1 = FC1 = 0	-	1.0	-	MHz
		FC1 = 0; FC1 = 1	-	2.0	-	MHz
		FC1 = 1; FC1 = 0	-	4.7	-	MHz
		FC1 =FC1 = 1	-	10	-	MHz
f_3dB(cutoff)(LPF)	LPF –3 dB cut-off frequency	FC1 = FC1 = 0	-	1.1	-	MHz
		FC1 = 0; FC1 = 1	-	2	-	MHz
		FC1 = 1; FC1 = 0	-	4.3	-	MHz
		FC1 =FC1 = 1	-	11	-	MHz
Vn(i)(eq)(preamp)	equivalent input noise voltage: preamplifier	$Z_{\text{source}} = 0 \ \Omega$	_	0.65	0.8	nV/√Hz

# TZA1000

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Z <sub>i</sub>	input impedance		1	1.84	4	kΩ
V <sub>I(6,7)</sub>	DC input voltage; pins 6 and 7		1.2	1.3	1.4	V
THD	total harmonic distortion	at 34 and 40 dB gain settings; V <sub>o(p-p)</sub> = 1 V	-	_	-40	dB
G <sub>v(servo)</sub>	servo preamplifier voltage gain	WX-WY to output	62	66	70	dB
V <sub>n(i)(eq)(servo)</sub>	equivalent input noise voltage: servo pre-amp	$Z_{source} = 0 \Omega$	-	1.8	2.8	nV/√Hz
V <sub>I(1,3))</sub>	DC input voltage pins 1 and 3		2.4	2.5	2.6	V
l <sub>sense</sub>	sense current	$R_{ref} = 430 \ \Omega; \ S = 64;$ note 3	14.6	15.2	15.8	mA
I <sub>sense(max)</sub>	maximum sense current	all conditions; note 4	33	-	-	mA
$\Delta V_{VDD3}$ -ISENSE	voltage difference between V <sub>DD3</sub> and ISENSE (pins 9 and 8)		1.6	-	13.2	V
RES <sub>DAC(SENSE)</sub>	sense DAC resolution		_	7	-	bits
Z <sub>o(sense)</sub>	output impedance of sense current source	f = 1 kHz; I <sub>o(sen)</sub> = 16 mA	10	-	-	kΩ
G <sub>v(FB)</sub>	FB amplifier voltage gain		11.5	13	14.5	dB
B <sub>(-3dB)</sub>	-3 dB bandwidth of FB amplifier		-	5	-	MHz
f <sub>coupling(FBamp)</sub>	-3 dB AC coupling of FB amplifier		-	3	-	kHz
I <sub>bias</sub>	bias current amplitude	ENFB1 = 0; ENFB0 = 1	-10	_	+10	mA
	(peak-to-peak)	ENFB1 = 1; ENFB0 = 0	0	_	+9	mA
		ENFB1 = ENFB0 = 1	-10	-	+20	mA
V <sub>O(23,24)</sub>	DC voltage level of FB outputs (pins 23 and 24)	B = 0; see Table 3	1.6	1.8	2.0	V
$\Delta V_{BIASA-BIASB}$	voltage difference between BIASA and BIASB (pins 23 and 24) at maximum DC bias voltage	B = 31; see Table 3; bias load 88 $\Omega$	1.4	1.52	1.6	V
RES <sub>DAC(BIAS)</sub>	bias DAC resolution		-	5	-	bits
V <sub>O(18,19)</sub>	read amplifier DC output voltage (pins 18 and 19)		2.4	2.5	2.6	V
ΔV <sub>OO(18,19)</sub>	read amplifier DC offset voltage (voltage change at pins 18 and 19)		-	-	100	mV
V <sub>o(rms)(18,19)</sub>	output voltage (RMS value; pins 18 and 19)		-	_	0.5	V
lo	guaranteed output current		1.5	-	-	mA
V <sub>O(AGCL)</sub>	lower AGC detection voltage level at OUTB		2.15	2.2	2.25	V
V <sub>O(AGCH)</sub>	upper AGC detection voltage level at OUTB		2.75	2.8	2.85	V

# TZA1000

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>hys(AGC)</sub>	hysteresis in AGC detection level		65	75	85	mV
B <sub>AGC</sub>	AGC bandwidth		_	1.5	-	MHz
f <sub>clk</sub>	operational clock	note 5	0	24	24	MHz
Write section						
l <sub>write</sub>	write current	$\label{eq:Rhead} \begin{array}{l} R_{\text{head}} = 10 \ \Omega; \\ R_{\text{ref}} = 430 \Omega; \\ \text{0-peak; W} = 32; \text{ note } 6 \end{array}$	27.3	28.8	30.3	mA
Iwrite(max)	maximum write current	$R_{head} = 10 \Omega; note 7$	60	80	-	mA
$\Delta I_{write}$	difference between positive and negative write currents	I <sub>write</sub> = 30 mA;	-	0	5	%
t <sub>t(iwrite)(Rload)</sub>	write current transition time	note 8				
	resistive load	resistive load, 10 $\Omega$	_	4	-	ns
	head load	$R_{head} = 10 \Omega;$ L <sub>head</sub> = 200 nH	-	6	12	ns
V <sub>o(p-p)(1,3)</sub>	output voltage swing (peak-to-peak value)		3	-	-	V
t <sub>R-W</sub>	read to write time		-	0.2	-	μs
t <sub>W-R</sub>	write to read time		-	10	-	μs
$\Delta t_{WD}$	WD pulse asymmetry	in WDI mode; note 9	_	0	1	ns
t <sub>WDIH</sub>	WDI pulse time HIGH		5	-	-	ns
t <sub>WDIL</sub>	WDI pulse time LOW		5	-	-	ns
R <sub>det(WUS)</sub>	WUS detection resistance level	short circuited to $V_{DD}$ or $V_{SS}$ ; $I_{write} = 30 \text{ mA}$	-	-	10	Ω
		open; I <sub>write</sub> = 30 mA	150	_	-	Ω

#### Notes

- 1. G is a 4-bit number contained in control bits G0 to G3 (see Table 12).
- 2. 6 dB step via a fixed setting, and 16 dB (in 1 dB steps) via AGC control.
- 3. S is a 7-bit number contained in control bits S0 to S6 (see Table 15).
- 4. The TZA1000 is guaranteed to operate reliably with sense currents of up to 33 mA.
- 5. The operational clock frequency (pin 15) must be >16 times higher the SCLK frequency to ensure reliable serial transfer.
- 6. W is a 7-bit number contained in control bits W0 to W6 (see Table 14). A more accurate calculation of the write current would be given by:  $I_c = I_t 0.003 \times I_t^2$ , where  $I_t = 125$  (W + 1) / 128,  $I_t$  the target current and  $I_c$  the write current.
- 7. The TZA1000 is guaranteed to supply a write current of up to 60 mA.
- 8. 10 to 90% of a total current reversal.
- 9. Difference between negative-to-positive and positive-to-negative current slopes.

# TZA1000

#### EQUIVALENT PIN CIRCUITS

PIN	DESCRIPTION	EQUIVALENT PIN CIRCUIT
1	write output stage	VDD (1) WX (1) WX (1) WX (1) MGG662
3	write output stage	VDD 
1,3,20	servo input configuration	WX 1 3 WY 700 Ω 2.5 V Vref 20 MGG664
6,7,20	input configuration	INA 6 5 kΩ 5 kΩ 5 kΩ 5 kΩ 5 kΩ MGG665
8	sense output configuration	12 V 50 Ω MGG666 (8) ISENSE

# TZA1000

PIN	DESCRIPTION	EQUIVALENT PIN CIRCUIT
10	digital input configuration	
11	digital input configuration	SDEN (1) MGG668
13	digital input configuration	HOLD (13) MGG669
14	digital input configuration	WGATE (14)
15	digital input configuration	

# TZA1000

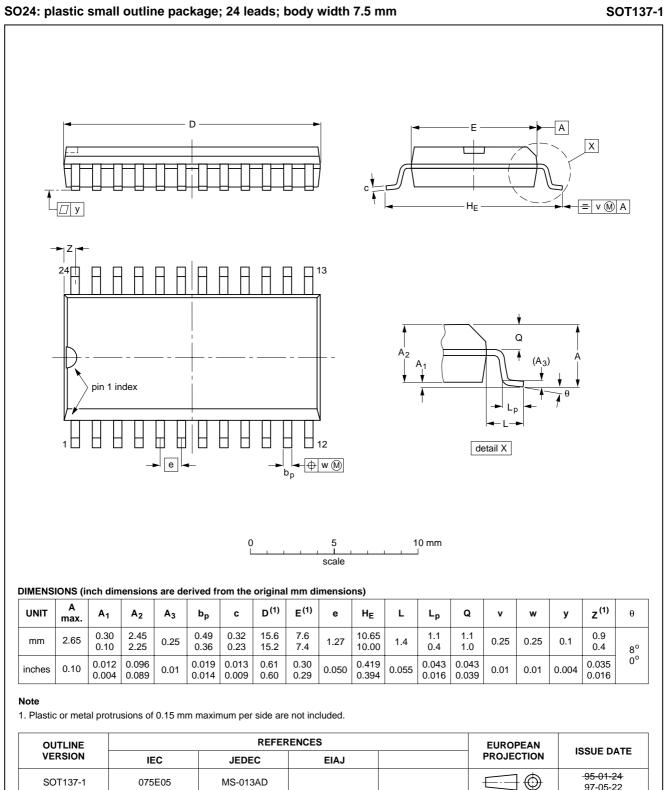
PIN	DESCRIPTION	EQUIVALENT PIN CIRCUIT
18	output configuration	VDD 25 Ω (18) OUTB 2.3 mA DC: 2.5 V MGG672
19	output configuration	$V_{DD}$ $25 \Omega$ $(19) OUTA$ $DC: 2.5 V$ $MGG673$
20	V <sub>ref</sub> output configuration	VDD 50 Ω (20) V <sub>ref</sub> 6 kΩ <i>MGG674</i>
22	reset output configuration	V <sub>DD</sub> (22) RESET 18 kΩ MGG675

TZA1000

97-05-22

# QIC read-write amplifier

#### PACKAGE OUTLINE



# TZA1000

#### SOLDERING

#### Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

#### **Reflow soldering**

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to  $250 \,^{\circ}$ C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

#### Wave soldering

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### **Repairing soldered joints**

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

TZA1000

#### DEFINITIONS

Data sheet status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification This data sheet contains final product specifications.		
Limiting values		
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

# TZA1000

NOTES

# Philips Semiconductors – a worldwide company

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB, Argentina: see South America Tel. +31 40 27 82785, Fax. +31 40 27 88399 Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113, New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +61 2 9805 4455, Fax. +61 2 9805 4466 Tel. +64 9 849 4160, Fax. +64 9 849 7811 Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010, Norway: Box 1, Manglerud 0612, OSLO, Fax. +43 160 101 1210 Tel. +47 22 74 8000, Fax. +47 22 74 8341 Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773 Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Belgium: see The Netherlands Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474 Brazil: see South America Poland: UI. Lukiska 10, PL 04-123 WARSZAWA, Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, Tel. +48 22 612 2831, Fax. +48 22 612 2327 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102 Portugal: see Spain Romania: see Italy Canada: PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381 Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 755 6918, Fax. +7 095 755 6919 China/Hong Kong: 501 Hong Kong Industrial Technology Centre, 72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231, Tel. +852 2319 7888, Fax. +852 2319 7700 Tel. +65 350 2538, Fax. +65 251 6500 Slovakia: see Austria Colombia: see South America Czech Republic: see Austria Slovenia: see Italy Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale, Tel. +45 32 88 2636, Fax. +45 31 57 0044 2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000, Tel. +27 11 470 5911, Fax. +27 11 470 5494 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920 South America: Al. Vicente Pinzon, 173, 6th floor, 04547-130 SÃO PAULO, SP, Brazil, France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex, Tel. +55 11 821 2333, Fax. +55 11 821 2382 Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427 Spain: Balmes 22 08007 BARCELONA Germany: Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +34 3 301 6312, Fax. +34 3 301 4107 Tel. +49 40 23 53 60, Fax. +49 40 23 536 300 Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM, Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS, Tel. +46 8 632 2000, Fax. +46 8 632 2745 Tel. +30 1 4894 339/239, Fax. +30 1 4814 240 Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Hungary: see Austria Tel. +41 1 488 2686, Fax. +41 1 488 3263 India: Philips INDIA Ltd, Band Box Building, 2nd floor, Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874 Tel. +91 22 493 8541, Fax. +91 22 493 0966 Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd. Indonesia: see Singapore 209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +66 2 745 4090, Fax. +66 2 398 0793 Tel. +353 1 7640 000, Fax. +353 1 7640 200 Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL, Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, Tel. +90 212 279 2770, Fax. +90 212 282 6707 TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007 Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7, Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557 United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Haves. Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421 Tel. +81 3 3740 5130, Fax. +81 3 3740 5077 United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +1 800 234 7381 Tel. +82 2 709 1412, Fax. +82 2 709 1415 Uruguay: see South America Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Vietnam: see Singapore Tel. +60 3 750 5214, Fax. +60 3 757 4880 Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD, Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +381 11 625 344, Fax.+381 11 635 777

Tel. +9-5 800 234 7381 Middle East: see Italy

For all other countries apply to: Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

Internet: http://www.semiconductors.philips.com

© Philips Electronics N.V. 1998

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

545102/00/02/pp24

Date of release: 1998 Mar 17

Document order number: 9397 750 03524

SCA57

Let's make things better.



